



CHENMKO ENTERPRISE CO.,LTD

CH451FPT

Lead free devices

SURFACE MOUNT

SCHOTTKY BARRIER DIODE

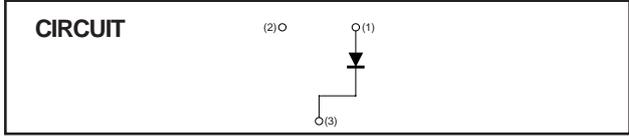
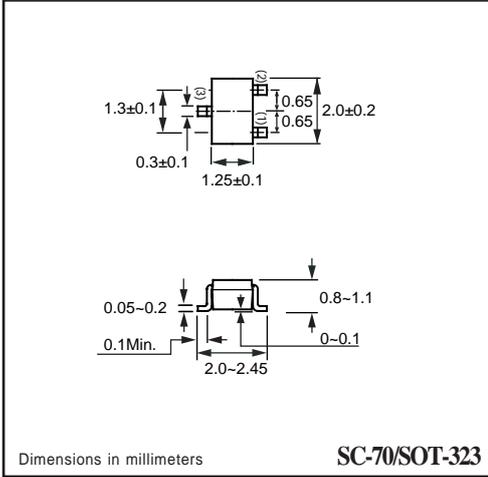
VOLTAGE 40 Volts CURRENT 0.1 Ampere

APPLICATION
* Low power rectification

FEATURE
* Small surface mounting type. (SC-70/SOT-323)
* Low VF. (VF=0.45V Typ. at 100mA)
* High reliability

CONSTRUCTION
* Silicon epitaxial planar

MARKING
* 3C



MAXIMUM RATINGS (At TA = 25°C unless otherwise noted)

RATINGS	SYMBOL	CH451FPT	UNITS
Maximum Recurrent Peak Reverse Voltage	VRRM	40	Volts
Maximum RMS Voltage	VRMS	28	Volts
Maximum DC Blocking Voltage	VDC	40	Volts
Maximum Average Forward Rectified Current	Io	0.1	Amps
Peak Forward Surge Current at 8.3 mSec single half sine-wave	IFSM	1.0	Amps
Typical Junction Capacitance between Terminal (Note 1)	CJ	6.0	pF
Maximum Operating Temperature Range	TJ	+125	°C
Storage Temperature Range	TSTG	-40 to +125	°C

ELECTRICAL CHARACTERISTICS (At TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	CH451FPT	UNITS
Maximum Instantaneous Forward Voltage at If(1)= 10mA	VF(1)	0.34	Volts
Maximum Instantaneous Forward Voltage at If(2)= 100mA	VF(2)	0.55	Volts
Maximum Average Reverse Current at Vr= 10V	IR	30	uAmps

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 10.0 volts.
2. ESD sensitive product handling required.

RATING CHARACTERISTIC CURVES (CH451FPT)

FIG. 1 - FORWARD CHARACTERISTICS

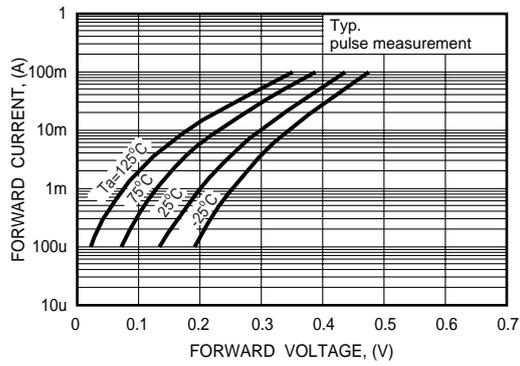


FIG. 2 - REVERSE CHARACTERISTICS

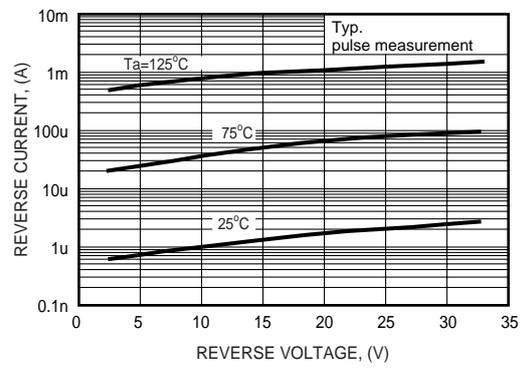


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

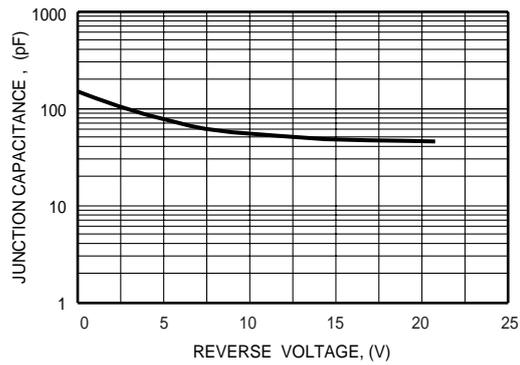


FIG. 4 - FORWARD POWER DISSIPATION CHARACTERISTICS

